

Abstract of the Disclosure

5 A magnetic random access memory (MRAM) comprises an  
array of magnetic memory cells arranged on a cross-point  
grid. Spurious voltages that build up on the stray wiring  
capacitance of unselected bit and word select lines are  
limited and discharged by diodes. The control of such  
spurious voltages improves device operating margins and  
allows the construction of larger arrays.